## **Constantinos Christofides**

## List of Publications by Year in Descending Order

Source: https://exaly.com/author-pdf/4320700/constantinos-christofides-publications-by-year.pdf

Version: 2024-04-28

This document has been generated based on the publications and citations recorded by exaly.com. For the latest version of this publication list, visit the link given above.

The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

78
papers

1,250
citations

h-index

80
ext. papers

21
h-index

22
g-index

4.11
ext. papers

avg, IF

L-index

#	Paper	IF	Citations
78	Ultrafast Spectroscopy and Red Emission from EGa2O 3/EGa 2S 3 Nanowires. <i>Nanoscale Research Letters</i> , <b>2015</b> , 10, 1016	5	12
77	Photophysics of PbS Quantum Dot Films Capped with Arsenic Sulfide Ligands. <i>Advanced Energy Materials</i> , <b>2014</b> , 4, 1301547	21.8	14
76	Ultrafast transient spectroscopy and photoluminescence properties of V2O5 nanowires. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 133112	3.4	16
75	Lost in the National Labyrinths of Bureaucracy: The Case of Renewable Energy Governance in Cyprus. <i>Lecture Notes in Energy</i> , <b>2013</b> , 169-181	0.4	
74	Carrier dynamics in EGa2O3 nanowires. <i>Journal of Applied Physics</i> , <b>2010</b> , 108, 124302	2.5	22
73	A systematic investigation into the conversion of EGa2O3 to GaN nanowires using NH3 and H2: Effects on the photoluminescence properties. <i>Journal of Applied Physics</i> , <b>2010</b> , 108, 124319	2.5	14
72	The Event and the Subject: The (IM)Possible Rehabilitation of Carl Schmitt. <i>Law and Critique</i> , <b>2010</b> , 21, 53-72	0.5	
71	Linear correlation between binding energy and Young modulus in graphene nanoribbons. <i>Journal of Applied Physics</i> , <b>2009</b> , 106, 054318	2.5	28
70	The role of humic substances in the formation of marble patinas under soil burial conditions. <i>Physics and Chemistry of Minerals</i> , <b>2009</b> , 36, 271-279	1.6	7
69	Photothermal hydrogen sensor: the technique, experimental process, and physicochemical analysis. <i>Applied Physics A: Materials Science and Processing</i> , <b>2008</b> , 92, 651-658	2.6	1
68	Photomodulated thermoreflectance microscopy applied on ion-implanted materials. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2008</b> , 5, 3767-3770		1
67	Laser induced micro-photoluminescence of marble and application to authenticity testing of ancient objects. <i>Applied Physics A: Materials Science and Processing</i> , <b>2007</b> , 90, 285-291	2.6	7
66	Instrumentation for the monitoring of toxic pollutants in water resources by means of neural network analysis of absorption and fluorescence spectra. <i>Sensors and Actuators B: Chemical</i> , <b>2007</b> , 121, 231-237	8.5	15
65	The role of surface vibrations and quantum confinement effect to the optical properties of very thin nanocrystalline silicon films. <i>Journal of Applied Physics</i> , <b>2007</b> , 102, 083534	2.5	29
64	Optical and structural properties of implanted Si wafers: the effects of implantation energy and subsequent isochronal annealing temperature. <i>Semiconductor Science and Technology</i> , <b>2006</b> , 21, 1059-1	1063	4
63	Study of the annealing kinetic effect and implantation energy on phosphorus-implanted silicon wafers using spectroscopic ellipsometry. <i>Journal of Applied Physics</i> , <b>2006</b> , 99, 123514	2.5	15
62	Spectroscopic ellipsometry as la lool for the loptical characterization and lageing studies of varnishes used in Post-Byzantine icon reconstructions. <i>Journal of Cultural Heritage</i> , <b>2006</b> , 7, 30-36	2.9	5

## (1997-2005)

61	Optical characterization of varnish films by spectroscopic ellipsometry for application in artwork conservation. <i>Applied Spectroscopy</i> , <b>2005</b> , 59, 94-9	3.1	6	
60	FULLSPECTRUM: a new PV wave making more efficient use of the solar spectrum. <i>Solar Energy Materials and Solar Cells</i> , <b>2005</b> , 87, 467-479	6.4	34	
59	Fine art painting characterization by spectroscopic ellipsometry: preliminary measurements on varnish layers. <i>Thin Solid Films</i> , <b>2004</b> , 455-456, 207-212	2.2	3	
58	Photomodulated thermoreflectance investigation at elevated temperatures: plasma versus thermal effect. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 1132-1134	3.4	O	
57	High-temperature photomodulated thermoreflectance measurements on phosphorus implanted and annealed silicon wafers. <i>Journal of Applied Physics</i> , <b>2003</b> , 94, 7121-7127	2.5	1	
56	Photomodulated thermoreflectance detection of hydrogen at elevated temperatures: a detection limit. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 904-906	3.4	4	
55	Ultrafast dynamics in phosphorus-implanted silicon wafers: The effects of annealing. <i>Physical Review B</i> , <b>2002</b> , 66,	3.3	9	
54	Spatial dependence of ultrafast carrier recombination centers of phosphorus-implanted and annealed silicon wafers. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 856-858	3.4	5	
53	Influence of temperature and modulation frequency on the thermal activation coupling term in laser photothermal theory. <i>Journal of Applied Physics</i> , <b>2002</b> , 92, 1280-1285	2.5	52	
52	Characterization of reflectivity inversion, <code>Hand</code> <code>phase</code> transitions and nanostructure formation in hydrogen activated thin Pd films on silicon based substrates. <i>Journal of Applied Physics</i> , 2002, 91, 3829-	-3 <del>8</del> 40	32	
51	Wear of a thin surface coating: modelling and experimental investigations. <i>Computational Materials Science</i> , <b>2002</b> , 25, 61-72	3.2	10	
50	Nondestructive evaluation of metal contaminated silicon wafers using radiometric measurements. <i>Journal of Applied Physics</i> , <b>1999</b> , 86, 3064-3067	2.5	1	
49	Photomodulated thermoreflectance investigation of semiconducting implanted wafers. <i>Microelectronic Engineering</i> , <b>1998</b> , 40, 251-261	2.5	1	
48	Temperature-induced reflectivity changes and activation of hydrogen sensitive optically thin palladium films on silicon oxide. <i>Review of Scientific Instruments</i> , <b>1998</b> , 69, 3331-3338	1.7	7	
47	Finite thickness and semi-infinite photothermal radiometric models for the characterization of semiconductors. <i>Applied Physics Letters</i> , <b>1998</b> , 72, 695-697	3.4	3	
46	Photomodulated thermoreflectance detection of hydrogen gas using optically thin palladium film on silicon oxide. <i>Review of Scientific Instruments</i> , <b>1998</b> , 69, 1505-1511	1.7	3	
45	Hydrogen gas detection via photothermal deflection measurement. <i>Review of Scientific Instruments</i> , <b>1997</b> , 68, 3544-3552	1.7	7	
44	Laser photothermal diagnostics of genuine and counterfeit British and United States banknotes.  Optical Engineering, 1997, 36, 400	1.1	3	

43	Thermoelectronic-wave coupling in laser photothermal theory of semiconductors at elevated temperatures. <i>Optical Engineering</i> , <b>1997</b> , 36, 459	1.1	111
42	Chapter 2 Transmission and Reflection Spectroscopy on Ion Implanted Semiconductors. Semiconductors and Semimetals, <b>1997</b> , 39-71	0.6	2
41	Chapter 3 Photoluminescence and Raman Scattering of Ion Implanted Semiconductors. Influence of Annealing. <i>Semiconductors and Semimetals</i> , <b>1997</b> , 46, 73-114	0.6	
40	Chapter 4 Photomodulated Thermoreflectance Investigation of Implanted Wafers. Annealing Kinetics of Defects. <i>Semiconductors and Semimetals</i> , <b>1997</b> , 46, 115-150	0.6	1
39	Two layer model for photothermal radiometry applied on semiconducting thin films. <i>Journal of Applied Physics</i> , <b>1997</b> , 82, 6220-6227	2.5	15
38	Photothermal radiometric and spectroscopic measurements on silicon nitride thin films. <i>Journal of Applied Physics</i> , <b>1997</b> , 82, 6215-6219	2.5	6
37	Noncontact Lifetime Reconstruction in Continuously Inhomogeneous Semiconductors: Generalized Theory and Experimental Photothermal Results for Ion-Implanted Si <b>1997</b> , 371-378		
36	Two-layer model for photomodulated thermoreflectance of semiconductor wafers. <i>Journal of Applied Physics</i> , <b>1996</b> , 80, 1713-1725	2.5	24
35	Multi-wavelength Raman probing of phosphorus implanted silicon wafers. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , <b>1996</b> , 117, 367-374	1.2	5
34	Photopyroelectric spectroscopy in the presence of an air gap transparent phase-shifter. <i>Applied Physics B: Lasers and Optics</i> , <b>1996</b> , 62, 563-574	1.9	2
33	Non-contacting measurements of photocarrier lifetimes in bulk- and polycrystalline thin-film Si photoconductive devices by photothermal radiometry. <i>Journal of Applied Physics</i> , <b>1996</b> , 80, 5332-5341	2.5	36
32	Photothermal measurements on amorphous thin films deposited on crystalline silicon. <i>Applied Physics Letters</i> , <b>1996</b> , 68, 538-540	3.4	3
31	Photothermal radiometric investigation of implanted silicon: The influence of dose and thermal annealing. <i>Applied Physics Letters</i> , <b>1996</b> , 69, 821-823	3.4	23
30	Statistical analysis of wind speed and direction in Cyprus. <i>Solar Energy</i> , <b>1995</b> , 55, 405-414	6.8	51
29	Infrared spectroscopy and electrical characterization of phosphorus implanted and annealed silicon layers. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , <b>1995</b> , 103, 46-55	1.2	2
28	Photothermal reflectance investigation of implanted silicon: The influence of thermal annealing. <i>Applied Physics Letters</i> , <b>1995</b> , 66, 3346-3348	3.4	11
27	Photothermal reflection versus temperature: Quantitative analysis. <i>Physical Review B</i> , <b>1995</b> , 51, 14115-	14.1,23	34
26	Photoluminescence measurements on phosphorus implanted silicon: Annealing kinetics of defects. Journal of Applied Physics, <b>1995</b> , 78, 796-800	2.5	4

25	Optical spectroscopy on implanted and annealed silicon wafers: Plasma resonance wavelength. <i>Journal of Applied Physics</i> , <b>1994</b> , 75, 3377-3384	2.5	7
24	Raman spectroscopy and spreading resistance analysis of phosphorus implanted and annealed silicon. <i>Journal of Applied Physics</i> , <b>1994</b> , 75, 8032-8038	2.5	30
23	Thermal wave photopyroelectric characterization of advanced materials: State of the art. <i>Critical Reviews in Solid State and Materials Sciences</i> , <b>1993</b> , 18, 113-174	10.1	18
22	Photopyroelectric detection of hydrogen/oxygen mixtures. <i>Review of Scientific Instruments</i> , <b>1993</b> , 64, 3563-3571	1.7	7
21	Annealing kinetics of defects of ion-implanted and furnace-annealed silicon layers: thermodynamic approach. <i>Semiconductor Science and Technology</i> , <b>1992</b> , 7, 1283-1294	1.8	21
20	COMPARISON BETWEEN MINI-SOLAR ENERGY STATIONS AND CONNECTION WITH ELECTRICAL GRID: THE INFLUENCE OF DISTANCES AND DIMENSIONS <b>1992</b> , 458-463		
19	Progress in hydrogen detection: A new photopyroelectric device. <i>International Journal of Hydrogen Energy</i> , <b>1991</b> , 16, 577-578	6.7	2
18	Optimization of the Photopyroelectric Hydrogen Gas Sensor: Geometry and Temperature Measurements. <i>Japanese Journal of Applied Physics</i> , <b>1991</b> , 30, 2916-2920	1.4	5
17	Photothermal electrostatics of the Pd-polyvinylidene fluoride photopyroelectric hydrogen gas sensor. <i>Journal of Applied Physics</i> , <b>1991</b> , 70, 4496-4504	2.5	13
16	Optical absorption coefficient and non-radiative quantum efficiency photopyroelectric spectra of pure crystal silicon from a single modulation frequency. <i>Ferroelectrics</i> , <b>1991</b> , 118, 411-424	0.6	9
15	Quantitative photopyroelectric out-of-phase spectroscopy of amorphous silicon thin films deposited on crystalline silicon. <i>Canadian Journal of Physics</i> , <b>1991</b> , 69, 317-323	1.1	12
14	Photopyroelectric (P2E) sensor for trace hydrogen gas detection. <i>Sensors and Actuators B: Chemical</i> , <b>1990</b> , 2, 79-87	8.5	17
13	Photothermal reflectance investigation of processed silicon. II. Signal generation and lattice temperature dependence in ion-implanted and amorphous thin layers. <i>Journal of Applied Physics</i> , <b>1990</b> , 67, 2822-2830	2.5	32
12	Infrared real-time-normalized photopyroelectric measurements of crystalline germanium: Instrumentation and spectroscopy. <i>Review of Scientific Instruments</i> , <b>1990</b> , 61, 2360-2367	1.7	21
11	Optimization and characterization of a differential photopyroelectric spectrometer. <i>Measurement Science and Technology</i> , <b>1990</b> , 1, 1363-1370	2	9
10	Surface hydrogenpalladium studies using a new photopyroelectric detector. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>1990</b> , 8, 3980-3983	2.9	10
9	Photothermal reflectance investigation of processed silicon. I. Room-temperature study of the induced damage and of the annealing kinetics of defects in ion-implanted wafers. <i>Journal of Applied Physics</i> , <b>1990</b> , 67, 2815-2821	2.5	44
8	Solid-state sensors for trace hydrogen gas detection. <i>Journal of Applied Physics</i> , <b>1990</b> , 68, R1-R30	2.5	182

7	Electronic transport investigation of arsenic-implanted silicon. I. Annealing influence on the transport coefficients. <i>Journal of Applied Physics</i> , <b>1989</b> , 65, 4832-4839	2.5	14
6	Electronic transport investigation of arsenic-implanted silicon. II. Annealing kinetics of defects. Journal of Applied Physics, 1989, 65, 4840-4844	2.5	15
5	Operating characteristics and comparison of photopyroelectric and piezoelectric sensors for trace hydrogen gas detection. I. Development of a new photopyroelectric sensor. <i>Journal of Applied Physics</i> , <b>1989</b> , 66, 3975-3985	2.5	22
4	Operating characteristics and comparison of photopyroelectric and piezoelectric sensors for trace hydrogen gas detection. II. Piezoelectric quartz-crystal microbalance sensor. <i>Journal of Applied Physics</i> , <b>1989</b> , 66, 3986-3992	2.5	23
3	Laser-induced photothermal reflectance investigation of silicon damaged by arsenic ion implantation: A temperature study. <i>Applied Physics Letters</i> , <b>1989</b> , 54, 2392-2394	3.4	23
2	Autonomous photovoltaic power system or connection with electrical grid? A preliminary feasibility study for small and isolated communities. <i>Solar Cells</i> , <b>1989</b> , 26, 165-175		5
1	Electronic transport investigations on silicon damaged by arsenic ion implantation. <i>Journal of Applied Physics</i> , <b>1986</b> , 60, 1699-1704	2.5	8